

# Silicon Carbide (SiC) Module – EliteSiC, 6 mohm SiC M1 MOSFET, 1200 V, 2-PACK Half Bridge Topology, F2 Package

## NXH006P120MNF2PTG

The NXH006P120MNF2 is a power module containing an 6 mΩ / 1200 V SiC MOSFET half-bridge and a thermistor in an F2 package.

### Features

- 6 mΩ / 1200 V SiC MOSFET Half-Bridge
- Thermistor
- Options with Pre-Applied Thermal Interface Material (TIM) and without Pre-Applied TIM
- Options with Solderable Pins and Press-Fit Pins
- These Devices are Pb-Free, Halide Free and are RoHS Compliant

### Typical Applications

- Solar Inverter
- Uninterruptible Power Supplies
- Electric Vehicle Charging Stations
- Industrial Power

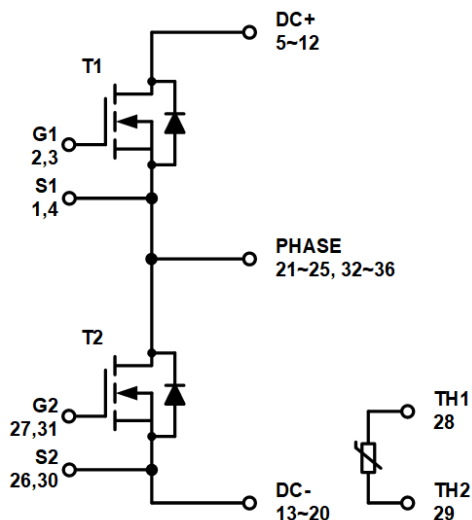
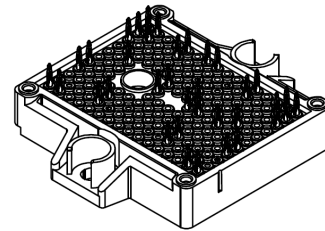


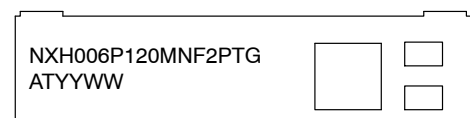
Figure 1. NXH006P120MNF2 Schematic Diagram

### PACKAGE PICTURE



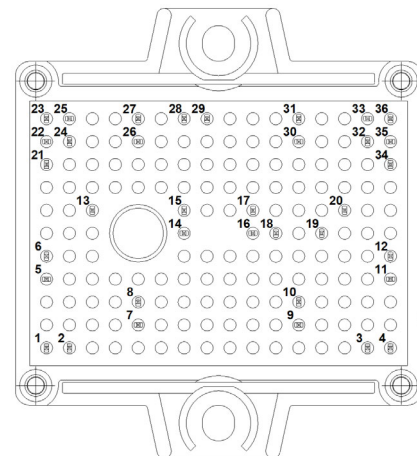
PIM36 56.7x42.5 (PRESS FIT)  
CASE 180BY

### MARKING DIAGRAM



XXXXX = Specific Device Code  
AT = Assembly & Test Site Code  
YWW = Year and Work Week Code

### PIN CONNECTIONS



See Pin Function Description for pin names

### ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

# NXH006P120MNF2PTG

## PIN FUNCTION DESCRIPTION

| Pin | Name  | Description                          |
|-----|-------|--------------------------------------|
| 1   | S1    | Q1 Kelvin Emitter (High side switch) |
| 2   | G1    | Q1 Gate (High side switch)           |
| 3   | G1    | Q1 Gate (High side switch)           |
| 4   | S1    | Q1 Kelvin Emitter (High side switch) |
| 5   | DC+   | DC Positive Bus connection           |
| 6   | DC+   | DC Positive Bus connection           |
| 7   | DC+   | DC Positive Bus connection           |
| 8   | DC+   | DC Positive Bus connection           |
| 9   | DC+   | DC Positive Bus connection           |
| 10  | DC+   | DC Positive Bus connection           |
| 11  | DC+   | DC Positive Bus connection           |
| 12  | DC+   | DC Positive Bus connection           |
| 13  | DC-   | DC Negative Bus connection           |
| 14  | DC-   | DC Negative Bus connection           |
| 15  | DC-   | DC Negative Bus connection           |
| 16  | DC-   | DC Negative Bus connection           |
| 17  | DC-   | DC Negative Bus connection           |
| 18  | DC-   | DC Negative Bus connection           |
| 19  | DC-   | DC Negative Bus connection           |
| 20  | DC-   | DC Negative Bus connection           |
| 21  | PHASE | Center point of half bridge          |
| 22  | PHASE | Center point of half bridge          |
| 23  | PHASE | Center point of half bridge          |
| 24  | PHASE | Center point of half bridge          |
| 25  | PHASE | Center point of half bridge          |
| 26  | S2    | Q2 Kelvin Emitter (Low side switch)  |
| 27  | G2    | Q2 Gate (Low side switch)            |
| 28  | TH1   | Thermistor Connection 1              |
| 29  | TH2   | Thermistor Connection 2              |
| 30  | S2    | Q2 Kelvin Emitter (Low side switch)  |
| 31  | G2    | Q2 Gate (Low side switch)            |
| 32  | PHASE | Center point of half bridge          |
| 33  | PHASE | Center point of half bridge          |
| 34  | PHASE | Center point of half bridge          |
| 35  | PHASE | Center point of half bridge          |
| 36  | PHASE | Center point of half bridge          |

# NXH006P120MNF2PTG

## MAXIMUM RATINGS

| Rating                                                                                                           | Symbol       | Value   | Unit               |
|------------------------------------------------------------------------------------------------------------------|--------------|---------|--------------------|
| <b>SiC MOSFET</b>                                                                                                |              |         |                    |
| Drain–Source Voltage                                                                                             | $V_{DS}$     | 1200    | V                  |
| Gate–Source Voltage                                                                                              | $V_{GS}$     | +25/–15 | V                  |
| Continuous Drain Current @ $T_c = 80^{\circ}\text{C}$ ( $T_J = 175^{\circ}\text{C}$ )                            | $I_D$        | 304     | A                  |
| Pulsed Drain Current ( $T_J = 175^{\circ}\text{C}$ ) (Note 2)                                                    | $I_{Dpulse}$ | 912     | A                  |
| Maximum Power Dissipation ( $T_J = 175^{\circ}\text{C}$ )                                                        | $P_{tot}$    | 950     | W                  |
| Short Circuit Withstand Time @ $V_{GE} = 15\text{ V}$ , $V_{CE} = 600\text{ V}$ , $T_J \leq 150^{\circ}\text{C}$ | $T_{sc}$     | 2.0     | $\mu\text{s}$      |
| Minimum Operating Junction Temperature                                                                           | $T_{JMIN}$   | –40     | $^{\circ}\text{C}$ |
| Maximum Operating Junction Temperature                                                                           | $T_{JMAX}$   | 175     | $^{\circ}\text{C}$ |

## THERMAL PROPERTIES

|                           |           |              |                    |
|---------------------------|-----------|--------------|--------------------|
| Storage Temperature Range | $T_{stg}$ | –40 to 150   | $^{\circ}\text{C}$ |
| TIM Layer Thickness       | $T_{TIM}$ | $160 \pm 20$ | $\mu\text{m}$      |

## INSULATION PROPERTIES

|                                                    |          |          |           |
|----------------------------------------------------|----------|----------|-----------|
| Isolation test voltage, $t = 1\text{ sec}$ , 60 Hz | $V_{is}$ | 4800     | $V_{RMS}$ |
| Creepage distance                                  |          | 12.7     | mm        |
| CTI                                                |          | 600      |           |
| Substrate Ceramic Material                         |          | HPS      |           |
| Substrate Ceramic Material Thickness               |          | 0.38     | mm        |
| Substrate Warpage (Note 3)                         | W        | Max 0.18 | mm        |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.
2. Calculated for 1 ms pulse, package limitation at 400 A.
3. Height difference between horizontal plane and substrate bottom copper.

## RECOMMENDED OPERATING RANGES

| Rating                                | Symbol | Min | Max | Unit               |
|---------------------------------------|--------|-----|-----|--------------------|
| Module Operating Junction Temperature | $T_J$  | –40 | 175 | $^{\circ}\text{C}$ |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## ELECTRICAL CHARACTERISTICS

$T_J = 25^{\circ}\text{C}$  unless otherwise noted

| Parameter                         | Test Conditions                                                             | Symbol       | Min   | Typ  | Max  | Unit             |
|-----------------------------------|-----------------------------------------------------------------------------|--------------|-------|------|------|------------------|
| <b>SiC MOSFET CHARACTERISTICS</b> |                                                                             |              |       |      |      |                  |
| Drain–Source Breakdown Voltage    | $V_{GS} = 0\text{ V}$ , $I_D = 800\text{ }\mu\text{A}$                      | $V_{(BR)DS}$ | 1200  | –    | –    | V                |
| Zero Gate Voltage Drain Current   | $V_{GS} = 0\text{ V}$ , $V_{DS} = 1200\text{ V}$                            | $I_{DSS}$    | –     | –    | 300  | $\mu\text{A}$    |
| Drain–Source On Resistance        | $V_{GS} = 20\text{ V}$ , $I_D = 200\text{ A}$ , $T_J = 25^{\circ}\text{C}$  | $R_{DS(ON)}$ | –     | 5.48 | 7.2  | $\text{m}\Omega$ |
|                                   | $V_{GS} = 20\text{ V}$ , $I_D = 200\text{ A}$ , $T_J = 125^{\circ}\text{C}$ |              | –     | 6.52 | –    |                  |
|                                   | $V_{GS} = 20\text{ V}$ , $I_D = 200\text{ A}$ , $T_J = 150^{\circ}\text{C}$ |              | –     | 7.28 | –    |                  |
| Gate–Source Threshold Voltage     | $V_{GS} = V_{DS}$ , $I_D = 80\text{ mA}$                                    | $V_{GS(TH)}$ | 1.8   | 2.83 | 4.3  | V                |
| Gate Leakage Current              | $V_{GS} = -10\text{ V} / 20\text{ V}$ , $V_{DS} = 0\text{ V}$               | $I_{GSS}$    | –1000 | –    | 1000 | nA               |

# NXH006P120MNF2PTG

## ELECTRICAL CHARACTERISTICS (continued)

T<sub>J</sub> = 25 °C unless otherwise noted

| Parameter                             | Test Conditions                                                                                                                    | Symbol                | Min | Typ  | Max | Unit |
|---------------------------------------|------------------------------------------------------------------------------------------------------------------------------------|-----------------------|-----|------|-----|------|
| <b>SiC MOSFET CHARACTERISTICS</b>     |                                                                                                                                    |                       |     |      |     |      |
| Input Capacitance                     | V <sub>DS</sub> = 800 V, V <sub>GS</sub> = 0 V, f = 1 MHz                                                                          | C <sub>ISS</sub>      | —   | 6687 | —   | pF   |
| Reverse Transfer Capacitance          |                                                                                                                                    | C <sub>RSS</sub>      | —   | 49   | —   |      |
| Output Capacitance                    |                                                                                                                                    | C <sub>OSS</sub>      | —   | 1092 | —   |      |
| Total Gate Charge                     | V <sub>DS</sub> = 800 V, V <sub>GS</sub> = 20 V, I <sub>D</sub> = 200 A                                                            | Q <sub>G(TOTAL)</sub> | —   | 847  | —   | nC   |
| Gate–Source Charge                    |                                                                                                                                    | Q <sub>GS</sub>       | —   | 231  | —   | nC   |
| Gate–Drain Charge                     |                                                                                                                                    | Q <sub>GD</sub>       | —   | 195  | —   | nC   |
| Turn–on Delay Time                    | T <sub>J</sub> = 25°C<br>V <sub>DS</sub> = 600 V, I <sub>D</sub> = 200 A<br>V <sub>GS</sub> = –5 V / 20 V, R <sub>G</sub> = 1.8 Ω  | t <sub>d(on)</sub>    | —   | 54   | —   | ns   |
| Rise Time                             |                                                                                                                                    | t <sub>r</sub>        | —   | 21   | —   |      |
| Turn–off Delay Time                   |                                                                                                                                    | t <sub>d(off)</sub>   | —   | 174  | —   |      |
| Fall Time                             |                                                                                                                                    | t <sub>f</sub>        | —   | 22   | —   |      |
| Turn–on Switching Loss per Pulse      |                                                                                                                                    | E <sub>ON</sub>       | —   | 2.1  | —   | mJ   |
| Turn–off Switching Loss per Pulse     |                                                                                                                                    | E <sub>OFF</sub>      | —   | 2.75 | —   |      |
| Turn–on Delay Time                    | T <sub>J</sub> = 150°C<br>V <sub>DS</sub> = 600 V, I <sub>D</sub> = 200 A<br>V <sub>GS</sub> = –5 V / 20 V, R <sub>G</sub> = 1.8 Ω | t <sub>d(on)</sub>    | —   | 48   | —   | ns   |
| Rise Time                             |                                                                                                                                    | t <sub>r</sub>        | —   | 19   | —   |      |
| Turn–off Delay Time                   |                                                                                                                                    | t <sub>d(off)</sub>   | —   | 196  | —   |      |
| Fall Time                             |                                                                                                                                    | t <sub>f</sub>        | —   | 22   | —   |      |
| Turn–on Switching Loss per Pulse      |                                                                                                                                    | E <sub>ON</sub>       | —   | 2.3  | —   | mJ   |
| Turn off Switching Loss per Pulse     |                                                                                                                                    | E <sub>OFF</sub>      | —   | 2.93 | —   |      |
| Diode Forward Voltage                 | I <sub>D</sub> = 200 A, T <sub>J</sub> = 25°C                                                                                      | V <sub>SD</sub>       | —   | 4.0  | 6   | V    |
|                                       | I <sub>D</sub> = 200 A, T <sub>J</sub> = 150°C                                                                                     |                       | —   | 3.6  | —   |      |
| Thermal Resistance – Chip–to–Case     | M1, M2                                                                                                                             | R <sub>thJC</sub>     | —   | 0.10 | —   | °C/W |
| Thermal Resistance – Chip–to–Heatsink | Thermal grease,<br>Thickness = 2 Mil +2%,<br>A = 2.8 W/mK                                                                          | R <sub>thJH</sub>     | —   | 0.21 | —   | °C/W |

## THERMISTOR CHARACTERISTICS

|                            |                          |                  |    |      |   |      |
|----------------------------|--------------------------|------------------|----|------|---|------|
| Nominal Resistance         | T = 25°C                 | R <sub>25</sub>  | —  | 5    | — | kΩ   |
|                            | T = 100°C                | R <sub>100</sub> | —  | 457  | — | Ω    |
| Deviation of R25           |                          | ΔR/R             | –3 | —    | 3 | %    |
| Power Dissipation          |                          | P <sub>D</sub>   | —  | 50   | — | mW   |
| Power Dissipation Constant |                          |                  | —  | 5    | — | mW/K |
| B–value                    | B(25/50), tolerance ±3%  |                  | —  | 3375 | — | K    |
| B–value                    | B(25/100), tolerance ±3% |                  | —  | 3455 | — | K    |

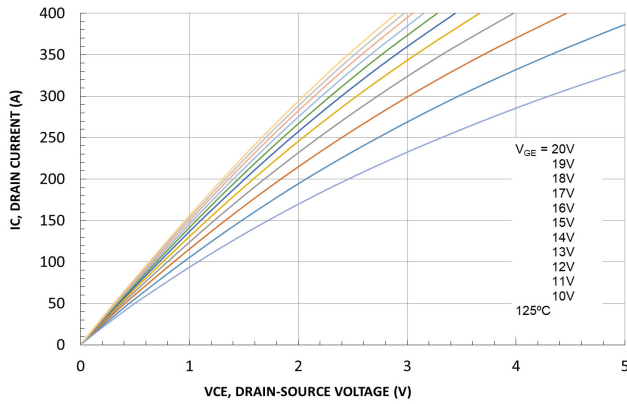
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## ORDERING INFORMATION

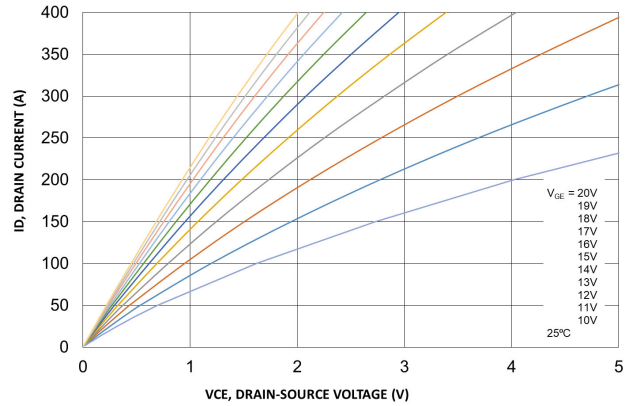
| Orderable Part Number | Marking           | Package                                                                                                                | Shipping                |
|-----------------------|-------------------|------------------------------------------------------------------------------------------------------------------------|-------------------------|
| NXH006P120MNF2PTG     | NXH006P120MNF2PTG | F2HALFBR: Case 180BY<br>Press–fit Pins with pre–applied<br>thermal interface material (TIM)<br>(Pb–Free / Halide Free) | 20 Units / Blister Tray |

# NXH006P120MNF2PTG

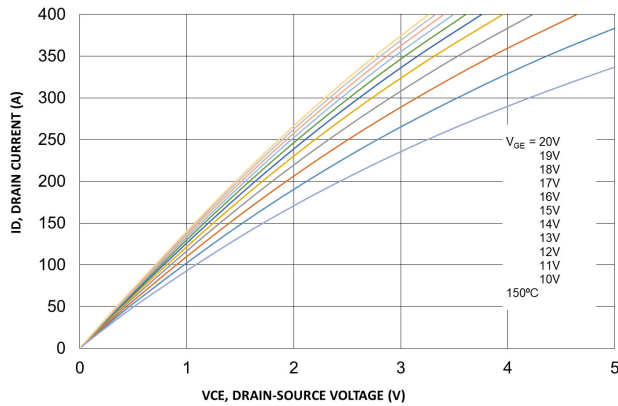
## TYPICAL CHARACTERISTICS HALFBIDGE MOSFET



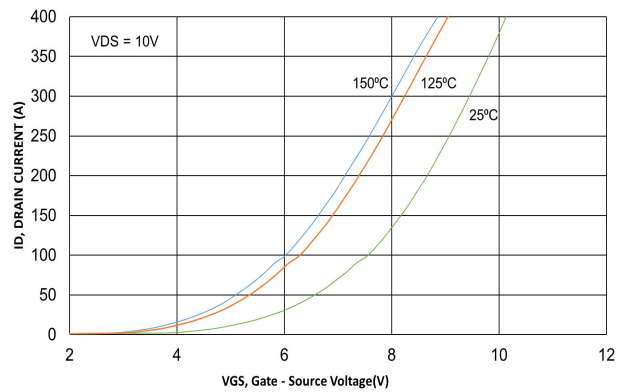
**Figure 2. MOSFET Typical Output Characteristic at 125°C**



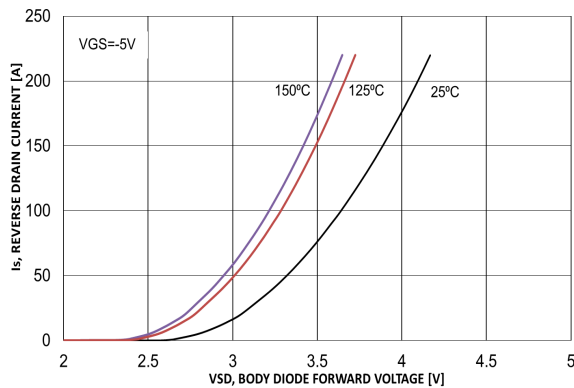
**Figure 3. MOSFET Typical Output Characteristic**



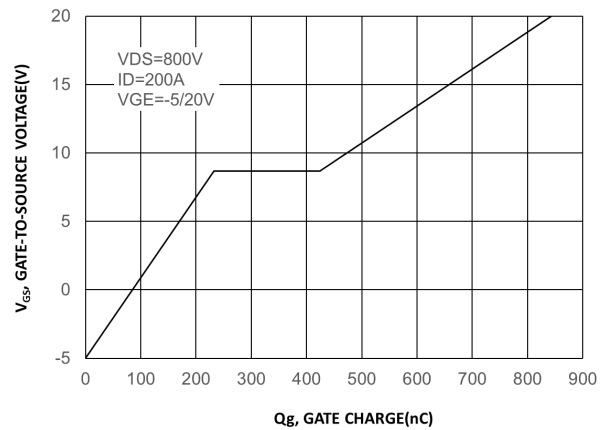
**Figure 4. MOSFET Typical Output Characteristic**



**Figure 5. MOSFET Typical Transfer Characteristic**



**Figure 6. Body Diode Forward Characteristic**



**Figure 7. Gate-to-Source Voltage vs. Total Charge**

# NXH006P120MNF2PTG

## TYPICAL CHARACTERISTICS

(25°C unless otherwise noted)

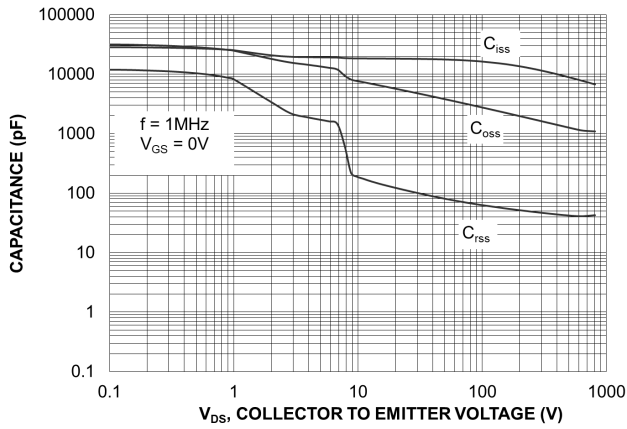


Figure 8. Capacitance vs. Drain-to-Source Voltage

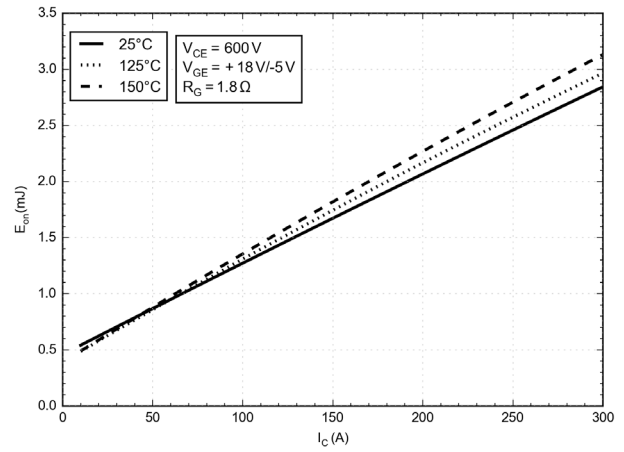


Figure 9. Typical Switching Loss Eon vs. IC

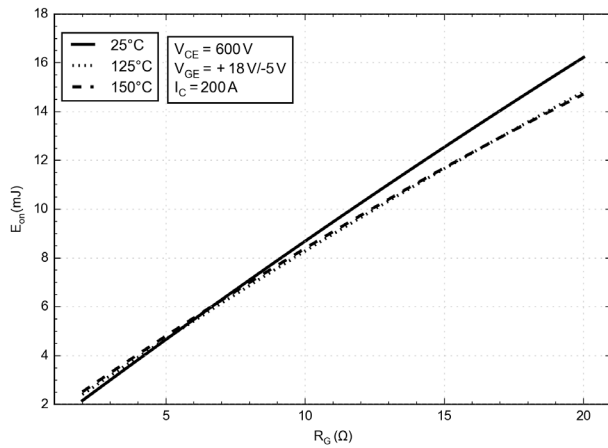


Figure 10. Typical Switching Loss Eon vs. Rg

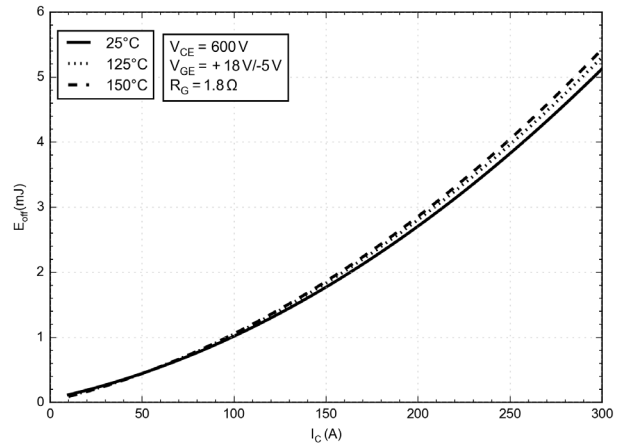


Figure 11. Typical Switching Loss Eoff vs. IC

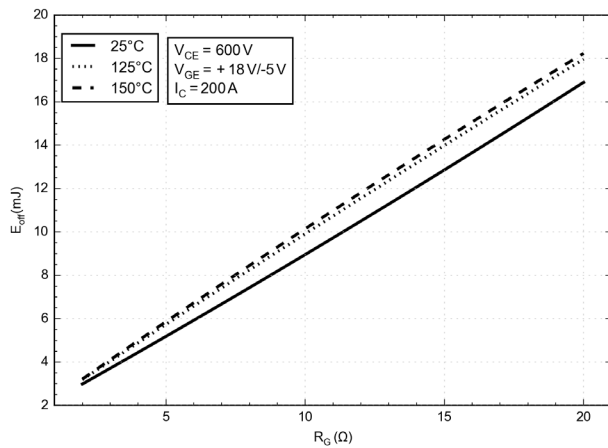


Figure 12. Typical Switching Loss Eoff vs. Rg

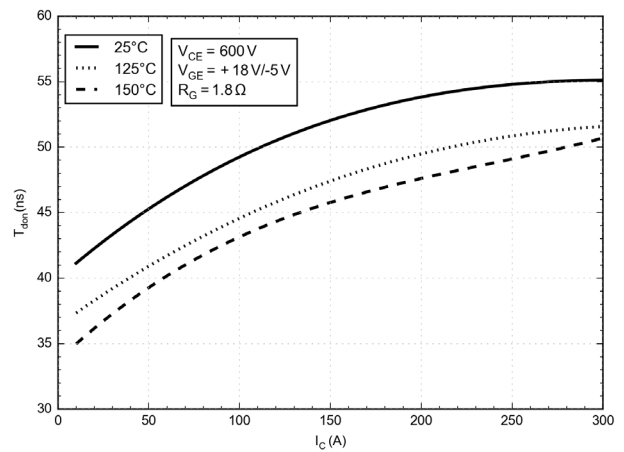


Figure 13. Typical Switching Loss Tdon vs. IC

# NXH006P120MNF2PTG

## TYPICAL CHARACTERISTICS

(25°C unless otherwise noted)

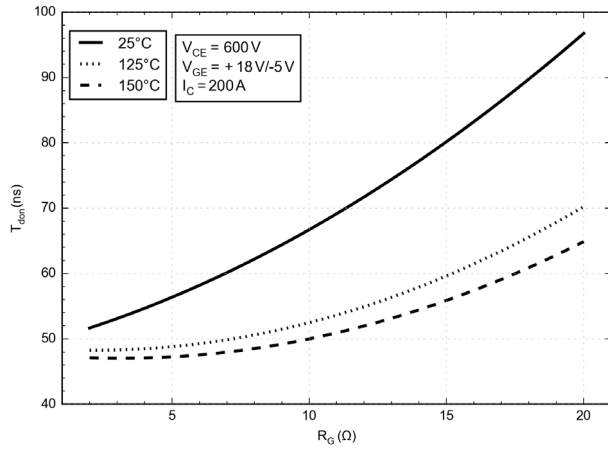


Figure 14. Typical Switching Loss Tdon vs. Rg

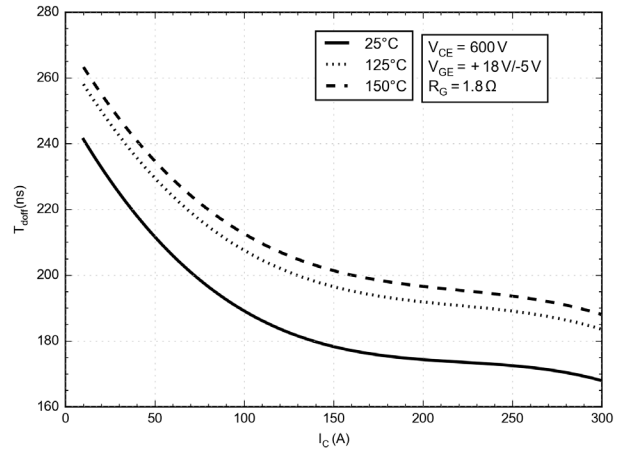


Figure 15. Typical Switching Loss Tdoff vs. IC

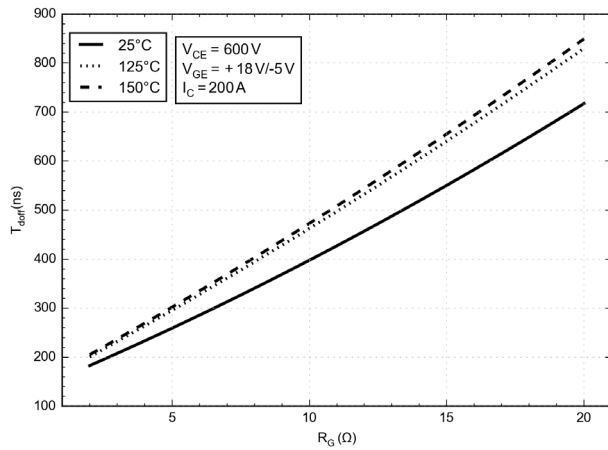


Figure 16. Typical Switching Loss Tdoff vs. Rg

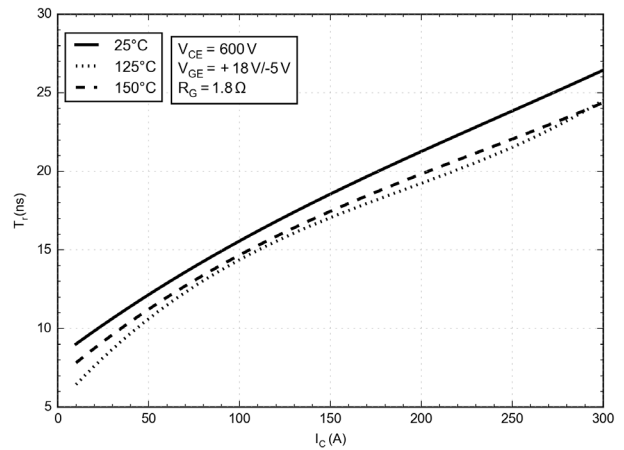


Figure 17. Typical Switching Loss Tr vs. IC

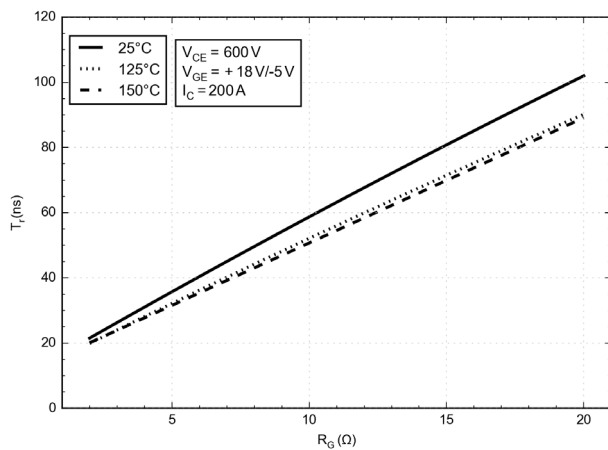


Figure 18. Typical Switching Loss Tr vs. Rg

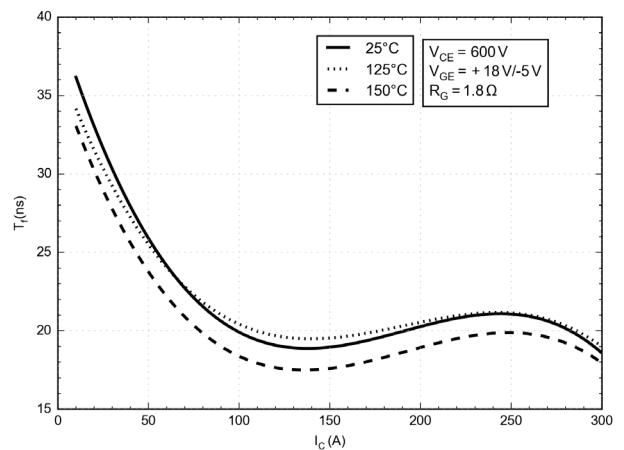


Figure 19. Typical Switching Loss Tf vs. IC

# NXH006P120MNF2PTG

## TYPICAL CHARACTERISTICS

(25°C unless otherwise noted)

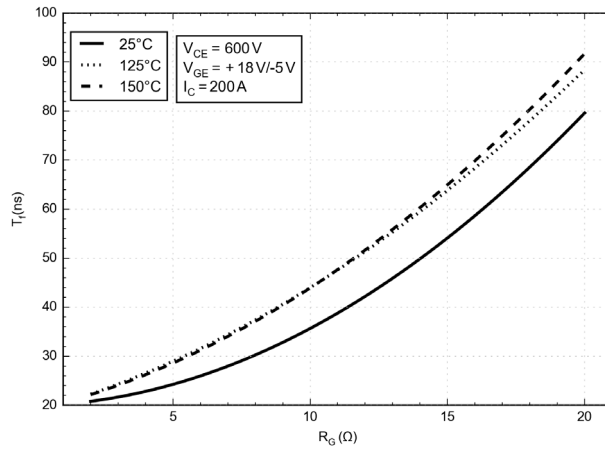


Figure 20. Typical Switching Loss  $T_f$  vs.  $R_g$

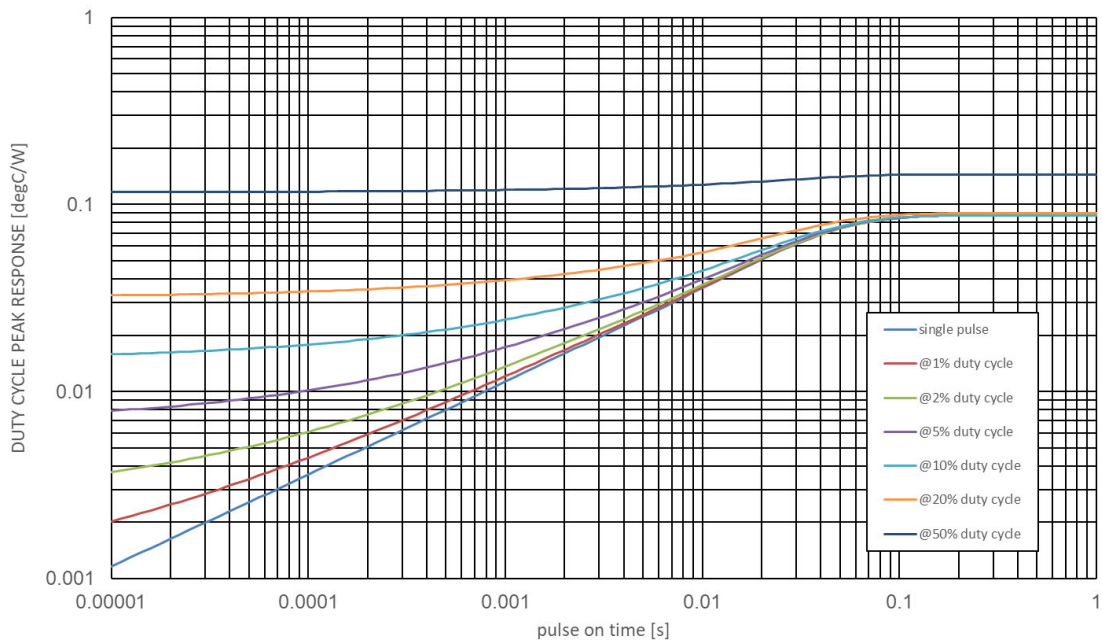
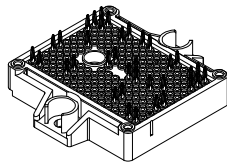
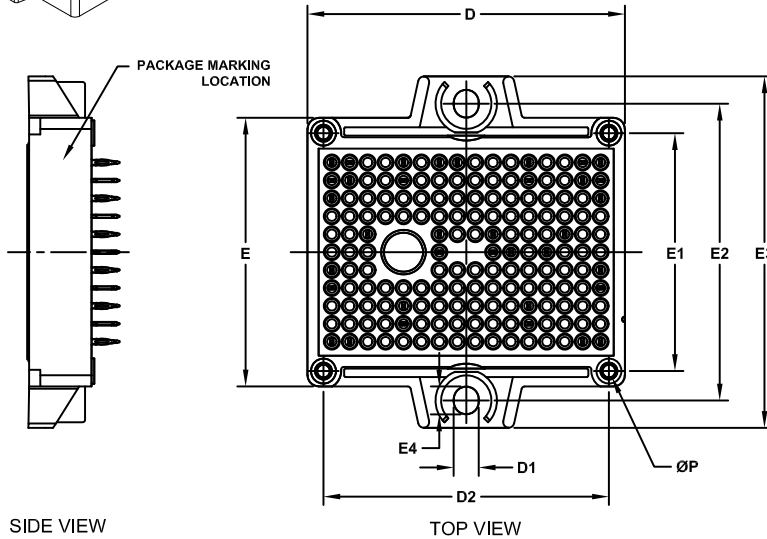


Figure 21. MOSFET Junction-to-Case Transient Thermal Impedance



PIM36 56.70x42.50x12.00  
CASE 180BY  
ISSUE E

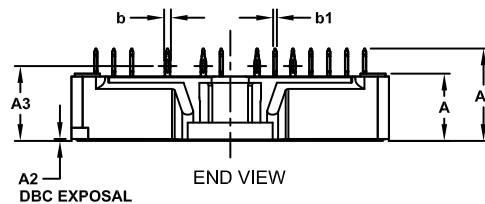
DATE 20 DEC 2023



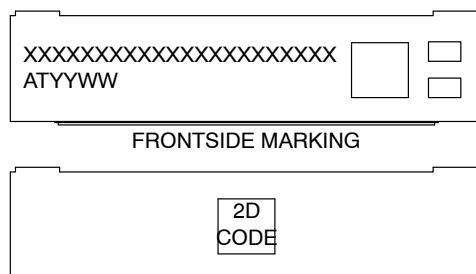
NOTES:

1. CONTROLLING DIMENSION: MILLIMETERS
2. PIN POSITION TOLERANCE IS  $\pm 0.4\text{mm}$
3. PRESS FIT PIN

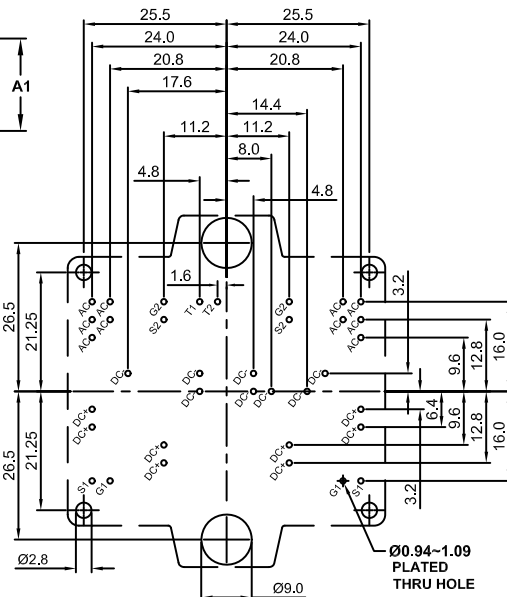
| DIM | MILLIMETERS |       |       |
|-----|-------------|-------|-------|
|     | MIN.        | NOM.  | MAX.  |
| A   | 11.65       | 12.00 | 12.35 |
| A1  | 16.10       | 16.50 | 16.90 |
| A2  | 0.00        | 0.35  | 0.60  |
| A3  | 12.95       | 13.35 | 13.75 |
| b   | 1.15        | 1.20  | 1.25  |
| b1  | 0.59        | 0.64  | 0.69  |
| D   | 56.40       | 56.70 | 57.00 |
| D1  | 4.40        | 4.50  | 4.60  |
| D2  | 50.85       | 51.00 | 51.15 |
| E   | 47.70       | 48.00 | 48.30 |
| E1  | 42.35       | 42.50 | 42.65 |
| E2  | 52.90       | 53.00 | 53.10 |
| E3  | 62.30       | 62.80 | 63.30 |
| E4  | 4.90        | 5.00  | 5.10  |
| P   | 2.20        | 2.30  | 2.40  |



GENERIC  
MARKING DIAGRAM\*



XXXXXX = Specific Device Code  
AT = Assembly & Test Site Code  
YYWW = Year and Work Week Code



RECOMMENDED  
MOUNTING PATTERN

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

|                  |                         |                                                                                                                                                                                  |
|------------------|-------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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| DESCRIPTION:     | PIM36 56.70x42.50x12.00 | PAGE 1 OF 1                                                                                                                                                                      |

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